

## EXPLANATION OF REFERENCE

101: LASER OSCILLATOR, 102: SLIT, 103: MIRROR, 104: BEAM, 105: CONVEX  
CYLINDRICAL LENS, 106: CONVEX CYLINDRICAL LENS, 107: SUBSTRATE,  
5 108: SUCTION STAGE, 109: X STAGE, 110: Y STAGE, 301: SLIT OPENING  
PORTION, 302: BLOCKING PLATE, 401: LASER, 402: LASER, 403:  
HALF-WAVEPLATE, 404: POLARIZING BEAM SPLITTER, 405: SLIT, 406:  
MIRROR, 407: MIRROR, 408: CONVEX CYLINDRICAL LENS, 409: CONVEX  
CYLINDRICAL LENS, 410: SEMICONDUCTOR FILM, 411: X STAGE, 412: Y  
10 STAGE, 501: SEMICONDUCTOR FILM, 502: LARGE CRYSTAL GRAIN REGION,  
600: LOWER ELECTRODE, 601: FIRST SUBSTRATE, 602: METAL FILM, 603:  
METAL OXIDE FILM, 604: SILICON OXIDE FILM, 605: CONDUCTIVE FILM,  
700: INSULATING FILM, 701: FIRST GATE INSULATING FILM, 701a: SILICON  
NITRIDE OXIDE FILM, 701b: SILICON OXYNITRIDE FILM, 702a: NON-SINGLE  
15 CRYSTAL SEMICONDUCTOR FILM, 702b: CRYSTALLINE SEMICONDUCTOR  
FILM, 703: SECOND GATE INSULATING FILM, 704: UPPER ELECTRODE, 704a:  
CONDUCTIVE FILM, 704b: CONDUCTIVE FILM, 705: RESIST MASK, 706:  
IMPURITY REGION, 707: SECOND CONDUCTIVE FILM, 900: LDD REGION,  
901: INSULATING FILM, 902: INTERLAYER INSULATING FILM, 903: WIRING,  
20 1000: SUBSTRATE, 1001: BASE FILM, 1002: NON-SINGLE CRYSTAL  
SEMICONDUCTOR FILM, 1003: LASER, 1004: CYLINDRICAL LENS, 1005:  
CYLINDRICAL LENS, 1006: CRYSTALLINE SEMICONDUCTOR FILM, 1007:  
SEMICONDUCTOR FILM, 1008: GATE INSULATING FILM, 1101: RESIST, 1102:  
CONDUCTIVE FILM, 1102a: FIRST CONDUCTIVE FILM, 1103: RESIST MASK,

1103a: RESIST MASK, 1003b: RESIST MASK, 1201: GATE ELECTRODE, 1301:  
SOURCE REGION, 1302: LOW-CONCENTRATION IMPURITY REGION, 1303:  
REGION WHERE LOW-CONCENTRATION IMPURITY REGION OVERLAPS TaN  
OF GATE ELECTRODE, 1304: CHANNEL REGION, 1305: DRAIN REGION, 1306:  
5 CHANNEL REGION, 1307: REGION OVERLAPPING TaN OF GATE ELECTRODE,  
1401: SOURCE REGION AND DRAIN REGION, 1402: CHANNEL REGION, 1403:  
REGION OVERLAPPING TaN OF GATE ELECTRODE, 1501: CAP OXIDE FILM,  
1502: INSULATING FILM, 1503: INSULATING FILM, 1504: WIRING, 1601:  
NON-SINGLE CRYSTAL SEMICONDUCTOR FILM, 1602a: NON-SINGLE  
10 CRSYTAL SEMICONDUCTOR FILM, 1602b: CRYSTALLINE SEMICONDUCTOR  
FILM, 1603: FIRST INSULATING FILM, 1604: MICROPARTICLE OF SILICON  
CRYSTAL, 1605: CONDUCTIVE FILM, 1606: FIRST CONDUCTIVE FILM, 1611:  
SECOND CONDUCTIVE FILM, 1612: SECOND CONDUCTIVE FILM, 1613:  
MASK PATTERN, 1621: GATE ELECTRODE, 1622: SECOND INSULATING  
15 LAYER, 1623: FLOATING GATE ELECTRODE, 1631: SOURCE REGION, 1632:  
DRAIN REGION, 1633: THIRD INSULATING FILM, 1634: FIRST INSULATING  
FILM, 1635: SOURCE ELECTRODE, 1636: DRAIN ELECTRODE, 1701: PARTICLE  
CONTAINING METAL ELEMENT, 1702: MICROPARTICLE CONTAINING  
SILICON CRYSTAL, 1703: SUBSTRATE, 1711: PARTICLE CONTAINING METAL  
20 ELEMENT, 1721: PARTICLE CONTAINING METAL ELEMENT, 1722: PARTICLE  
CONTAINING METAL ELEMENT, 1723: PARTICLE CONTAINING METAL  
ELEMENT, 1801: INSULATING SUBSTRATE, 1802: SEMICONDUCTOR FILM,  
1803: HIGH-CONCENTRATION IMPURITY ELEMENT, 1804: CHANNEL  
REGION, 1805: GATE INSULATING FILM, 1806: GATE ELECTRODE, 1808:

INSULATED REGION, 1901: CASE, 1902: SUPPORTING STAND, 1903: DISPLAY  
PORTION, 1904: SPEAKER PORTION, 1905: VIDEO INPUT TERMINAL, 1911:  
CASE, 1912: DISPLAY PORTION, 1913: KEYBOARD, 1914: EXTERNAL  
CONNECTION PORT, 1915: POINTING MOUSE, 1921: CASE, 1922: DISPLAY  
5 PORTION, 1923: OPERATION KEY, 1941: PASSPORT, 1942: RADIO FREQUENCY  
IC TAG, 1951: RADIO FREQUENCY IC TAG, 1952: READER, 1953: ANTENNA  
PORTION, 2001: BEAM SPOT, 2002: ENERGY DENSITY DISTRIBUTION, 2003:  
CENTRAL REGION OF BEAM SPOT, 2004: END PORTION OF BEAM SPOT,  
2100: SEMICONDUCTOR FILM, 2101: SOURCE SIGNAL LINE, 2102: GATE  
10 SIGNAL LINE, 2103: CURRENT SUPPLYING LINE, 2104: SWITCHING TFT, 2105:  
DRIVER TFT, 2106: CAPACITOR, 2107: LIGHT-EMITTING ELEMENT, 2109:  
MICROCRYSTAL REGION, 2201: MICROCRYSTAL REGION, 2701: DISPLAY  
PANEL, 2702: PRINT SUBSTRATE, 2703: PIXEL PORTION, 2704: FIRST  
SCANNING LINE DRIVER CIRCUIT, 2705: SECOND SCANNING LINE DRIVER  
15 CIRCUIT, 2706: SIGNAL LINE DRIVER CIRCUIT, 2707: CONTROLLER, 2708:  
CENTRAL PROCESSING UNIT, 2709: MEMORY, 2710: POWER SUPPLY CIRCUIT,  
2711: AUDIO PROCESSING CIRCUIT, 2712: SENDING/RECEIVING CIRCUIT,  
2713: FLEXIBLE WIRING SUBSTRATE, 2714: INTERFACE (I/F) PORTION, 2715:  
ANTENNA PORT, 2716: VRAM, 2717: DRAM, 2718: FLASH MEMORY, 2719:  
20 INTERFACE, 2720: CONTROL SIGNAL GENERATING CIRCUIT, 2721:  
DECODER, 2722: RESISTOR, 2723: ARITHMETIC CIRCUIT, 2724:VRAM, 2725:  
INPUT MEANS, 2726: MICROPHONE, 2727: SPEAKER, 2728: ANTENNA